



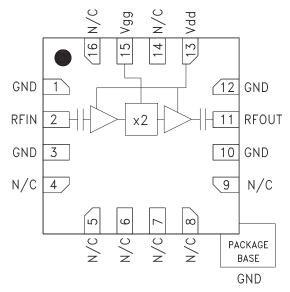
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Typical Applications

The HMC561LP3E are suitable for:

- Clock Generation Applications: SONET OC-192 & SDH STM-64
- Point-to-Point & VSAT Radios
- Test Instrumentation
- Military & Space

Functional Diagram



SMT GaAs MMIC x2 ACTIVE FREQUENCY MULTIPLIER, 8 - 21 GHz OUTPUT

Features

High Output Power: +14 dBm Low Input Power Drive: 0 to +6 dBm Fo Isolation: 15 dBc @ Fout= 16 GHz 100 KHz SSB Phase Noise: -139 dBc/Hz RoHS Compliant 3x3 mm SMT Package

General Description

The HMC561LP3(E) is a x2 active broadband frequency multiplier utilizing GaAs PHEMT technology in a leadless RoHS compliant SMT package. When driven by a +5 dBm signal, the multiplier provides +14 dBm typical output power from 8 to 21 GHz and the Fo and 3Fo isolations are 15 dBc at 16 GHz. The HMC561LP3(E) is ideal for use in LO multiplier chains for Pt to Pt & VSAT Radios yielding reduced parts count vs. traditional approaches. The low additive SSB Phase Noise of -139 dBc/Hz at 100 kHz offset helps maintain good system noise performance. The RoHS packaged HMC561LP3(E) eliminates the need for wire bonding, and allows the use of surface mount manufacturing techniques. For availability on Non-RoHS compliant HMC561LP3 product please contact Hittite Microwave sales directly.

Electrical Specifications, $T_{A} = +25^{\circ}C$, Vdd = +5V, 5 dBm Drive Level

Parameter		Тур.	Max.	Units
Frequency Range, Input		4 - 10.5		
Frequency Range, Output		8 - 21		GHz
Output Power	11	11 14		
Fo Isolation (with respect to output level)		15		dBc
3Fo Isolation (with respect to output level)		15		dBc
4Fo Isolation (with respect to output level)		20		dBc
Input Return Loss		16		dB
Output Return Loss		8		dB
SSB Phase Noise (100 kHz Offset)		-139		dBc/Hz
Supply Current (Idd) (Vdd = 5V, Vgg = -1.7V Typ.)		98		mA

*Adjust Vgg between -2.0 and -1.2V to achieve Idd = 98 mA

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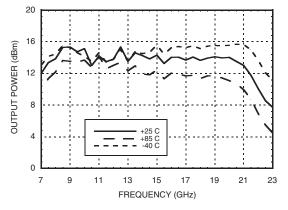




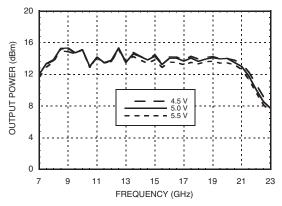
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Output Power vs. Temperature @ 5 dBm Drive Level

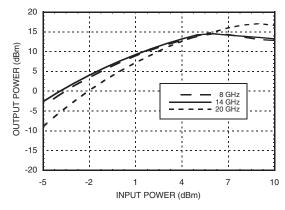
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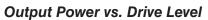


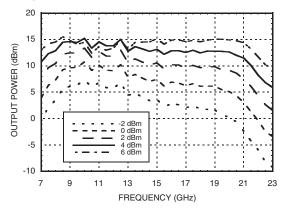
Output Power vs. Supply Voltage @ 5 dBm Drive Level



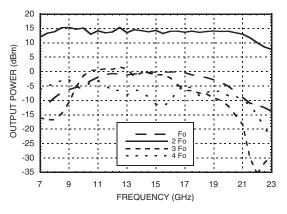
Output Power vs. Input Power



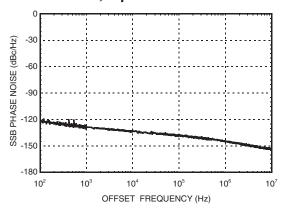




Isolation @ 5 dBm Drive Level



SSB Phase Noise Performance, Fout= 16 GHz, Input Power = +3 dBm

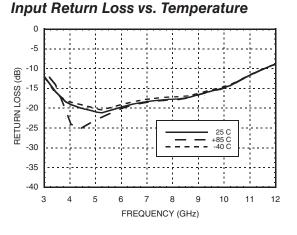


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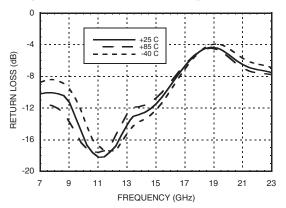


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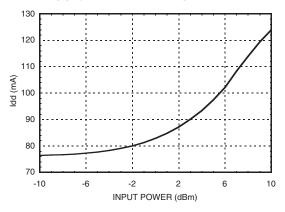


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Output Return Loss vs. Temperature



Supply Current vs. Input Power



Absolute Maximum Ratings

RF Input (Vdd = +5V)	+10 dBm
Supply Voltage (Vdd)	+5.5 Vdc
Channel Temperature	150 °C
Continuous Pdiss (T= 85 °C) (derate 9.8 mW/°C above 85 °C)	635 mW
Thermal Resistance (channel to ground paddle)	102 °C/W
Storage Temperature	-65 to +150 °C
Operating Temperature	-40 to +85 °C

Typical Supply Current vs. Vdd

Vdd (Vdc)	ldd (mA)
4.5	97
5.0	98
5.5	99

Note:

Multiplier will operate over full voltage range shown above.



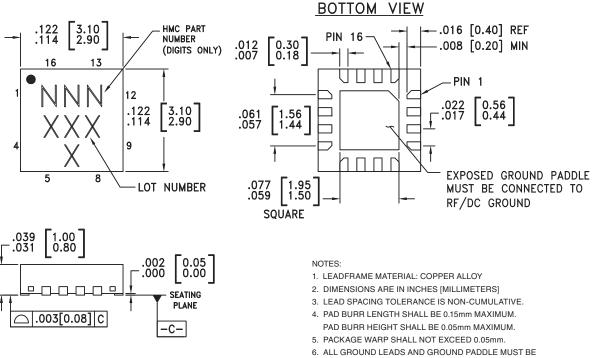
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SMT GaAs MMIC x2 ACTIVE FREQUENCY MULTIPLIER, 8 - 21 GHz OUTPUT



Outline Drawing



SOLDERED TO PCB RF GROUND. 7. REFER TO HITTITE APPLICATION NOTE FOR SUGGESTED LAND PATTERN.

Package Information

Part Number	Package Body Material	Lead Finish	MSL Rating	Package Marking ^[3]
HMC561LP3	Low Stress Injection Molded Plastic [4]	Sn/Pb Solder	MSL1 ^[1]	561 XXXX
HMC561LP3E	RoHS-compliant Low Stress Injection Molded Plastic	100% matte Sn	MSL1 ^[2]	<u>561</u> XXXX

[1] Max peak reflow temperature of 235 $^\circ\text{C}$

[2] Max peak reflow temperature of 260 $^\circ\text{C}$

[3] 4-Digit lot number XXXX

[4] For availability on Non-RoHS HMC561LP3 products please contact Hittite Microwave sales directly.

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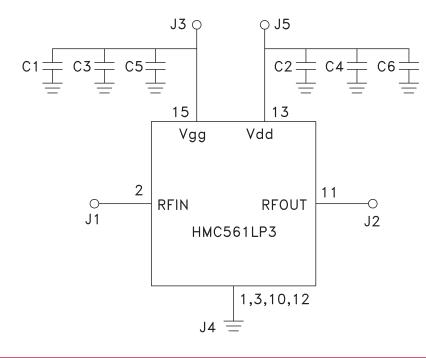


SMT GaAs MMIC x2 ACTIVE FREQUENCY MULTIPLIER, 8 - 21 GHz OUTPUT

Pin Description

Pin Number	Function	Description	Interface Schematic
1, 3, 10, 12	GND	Package bottom must also be connected to RF/DC ground.	GND =
2	RFIN	Pin is AC coupled and matched to 50 Ohms.	
4 - 9, 14, 16	N/C	These pins are internally not connected; however, this product was specified with these pins connected to RF/ DC ground.	
11	RFOUT	Pin is AC coupled and matched to 50 Ohms.	
13	Vdd	Supply voltage 5V \pm 0.5V. External bypass capacitors of 100 pF, 1,000 pF and 2.2 μF are required.	Vdd
15	Vgg	Gate control for multiplier. Adjust to achieve Idd of 98 mA. Please follow "MMIC Amplifier Biasing Procedure" Application note.	Vgg o

Application Circuit



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Component	Value
C1, C2	100 pF
C3, C4	1,000 pF
C5, C6	2.2 μF

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